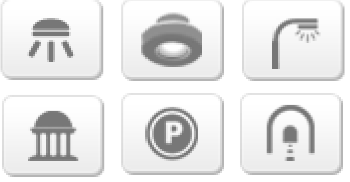
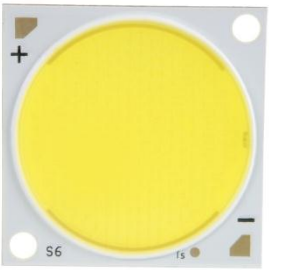
Enable High Flux and Cost Efficient System

Z Power Chip on board – ZC series

SDWx7F1C (SDW07F1C, SDW87F1C)





MacAdam 3-Step

RoHS

Product Brief

Description

- The ZC series are LED arrays which provide High Flux and High Efficacy.
- It is especially designed for easy assembly of Lighting fixtures by eliminating reflow soldering process.
- It's thermal management is excellent than other power LED solutions with wider Metal area.
- ZC series are ideal light sources for General Lighting applications including Replacement Lamps, Industrial & Commercial Lightings and other high Lumen required applications.

Features and Benefits

- Size 38mm * 38 mm
- High Efficacy typ. 150 lm/W
- Flux range from 2,000~19,000lm
- Power dissipation 15~ 160W
- Maximum current
- 3000K CCT with CRI 80
- Uniformed Shadow
- Excellent Thermal management

Key Applications

- Commercial – Downlight
- Out door area – High/Low Bay lighting, Street lighting, Tunnel lighting
- Architectural
- Industrial – High/Low Bay lighting

Table 1. Product Selection Table

Part Number	CCT [K]			
	Color	Min.	Typ.	Max.
SDW07F1C	Cool White	4700	-	6000
SDW87F1C	Warm White	2600	-	4200

Table of Contents

Performance Characteristics

Table 2-1. Electro Optical Characteristics, T_j=25ºC

Part Number	CCT (K) [1]	Typical Luminous Flux [2] Φ_V [3] (lm)	Typical Forward Voltage (V)	CRI [5], R_a	Viewing Angle (degrees) 2Θ ½
	Typ.	1.5A	1.5A	Min.	Typ.
SDW07F1C	5000	11,800	53	70	124
SDW87F1C	4000	11,400	53	80	124
	3000	11,000	53	80	124
	2700	10,500	53	80	124

Table 2-2. Electro Optical Characteristics, T_j=85ºC

Part Number	CCT (K) [1]	Typical Luminous Flux [2] Φ_V [3] (lm)	Typical Forward Voltage (V)	CRI [5], R_a	Viewing Angle (degrees) 2Θ ½
	Typ.	1.5A	1.5A	Min.	Typ.
SDW07F1C	5000	10,600	51.3	70	124
SDW87F1C	4000	10,250	51.3	80	124
	3000	9,900	51.3	80	124
	2700	9,400	51.3	80	124

Notes :

1. Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram. Color coordinate : ±0.005, CCT ±5% tolerance.
2. Seoul Semiconductor maintains a tolerance of ±7% on flux and power measurements.
3. Φ_V is the total luminous flux output as measured with an integrating sphere.
4. Tolerance is ±3% on forward voltage measurements.
5. Tolerance is ±2 on CRI measurements.

* No values are provided by real measurement. Only for reference purpose.

Performance Characteristics

Table 2-3. Electro Optical Characteristics, T_j=25ºC

Part Number	CCT (K) [1]	Typical Luminous Flux [2] Φ_V [3] (lm)	Typical Forward Voltage (V)	CRI [5], R_a	Viewing Angle (degrees) 2Θ ½
	Typ.	1.8A	1.8A	Min.	Typ.
SDW07F1C	5000	13,750	53.6	70	124
SDW87F1C	4000	13,300	53.6	80	124
	3000	12,750	53.6	80	124
	2700	12,200	53.6	80	124

Table 2-4. Electro Optical Characteristics, T_j=85ºC

Part Number	CCT (K) [1]	Typical Luminous Flux [2] Φ_V [3] (lm)	Typical Forward Voltage (V)	CRI [5], R_a	Viewing Angle (degrees) 2Θ ½
	Typ.	1.8A	1.8A	Min.	Typ.
SDW07F1C	5000	12,370	51.9	70	124
SDW87F1C	4000	11,970	51.9	80	124
	3000	11,475	51.9	80	124
	2700	11,000	51.9	80	124

Notes :

1. Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram. Color coordinate : ±0.005, CCT ±5% tolerance.
2. Seoul Semiconductor maintains a tolerance of ±7% on flux and power measurements.
3. Φ_V is the total luminous flux output as measured with an integrating sphere.
4. Tolerance is ±3% on forward voltage measurements.
5. Tolerance is ±2 on CRI measurements.

* No values are provided by real measurement. Only for reference purpose.

Performance Characteristics

Table 3. Absolute Maximum Characteristics, T_j=25ºC

Parameter	Symbol	Value			Unit
		Min.	Typ.	Max.	
Forward Current	I_F	-	1.5	3.0	A
Power Dissipation	P_d	-	80	170	W
Junction Temperature [1]	T_j	-	-	125	ºC
Operating Temperature	T_{opr}	-40	-	85	ºC
Surface Temperature	T_S	-	-	100	ºC
Storage Temperature	T_{stg}	-40	-	100	ºC
Thermal resistance (J to S)	Rth_{JS}	-	0.2	-	K/W
ESD Sensitivity(HBM) [2]	-	-	-	±8	kV

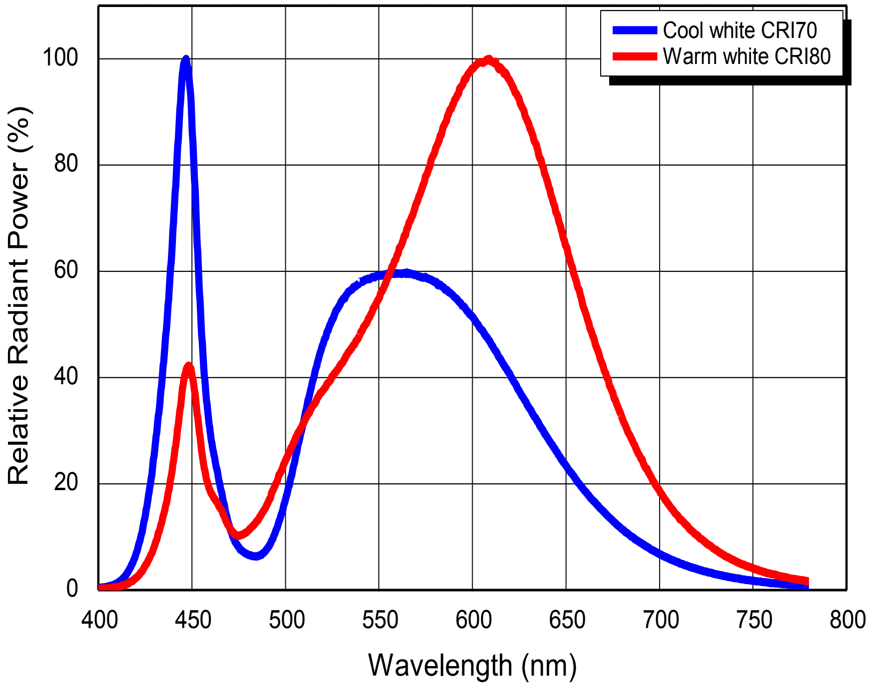
Notes :

1. $I_F \leq 3A$
2. A zener diode is included to protect the product from ESD.
3. Thermal resistance : Rth_{JS} (Junction / solder)

- LED’s properties might be different from suggested values like above and below tables if operation condition will be exceeded our parameter range. Care is to be taken that power *dissipation does not* exceed the absolute maximum rating of the product.
- Thermal resistance can be increased substantially depending on the heat sink design/operating condition, and the maximum possible driving current will decrease accordingly.
- All measurements were made under the standardized environment of Seoul Semiconductor.

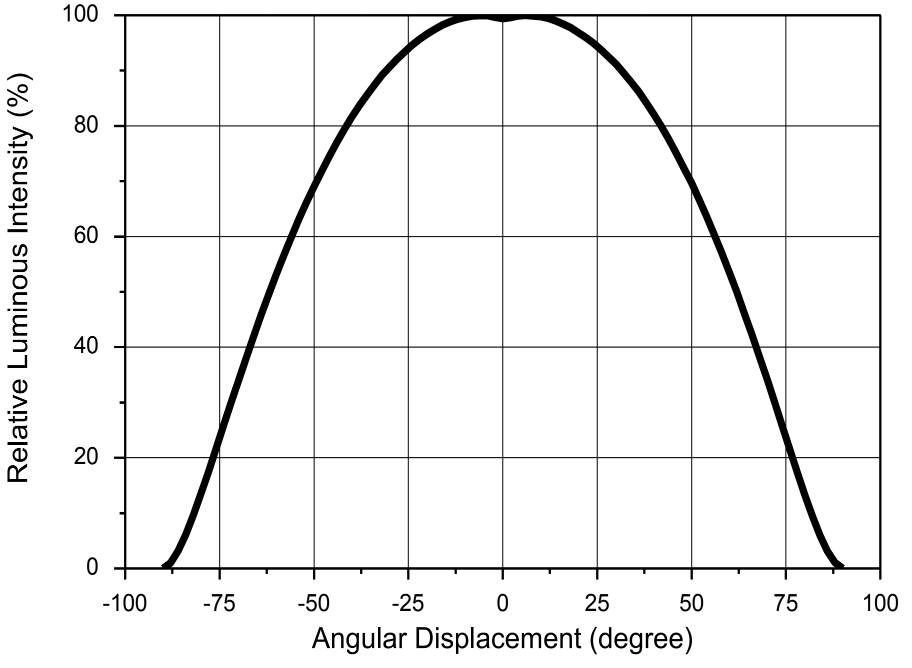
Characteristics Graph

Fig 1. Color Spectrum, T_j=25℃, I_F=1.5A



Characteristics Graph

Fig 2. Radiant pattern, T_j=25℃, I_F=1.5A



Characteristics Graph

Fig 3. Forward Voltage vs. Forward Current, T_j=25℃

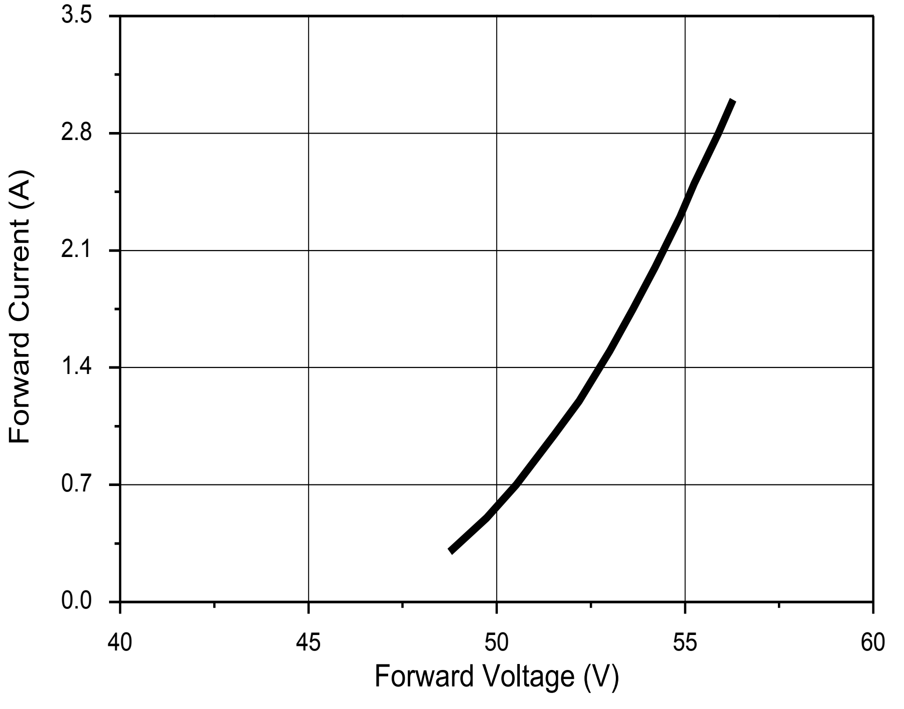
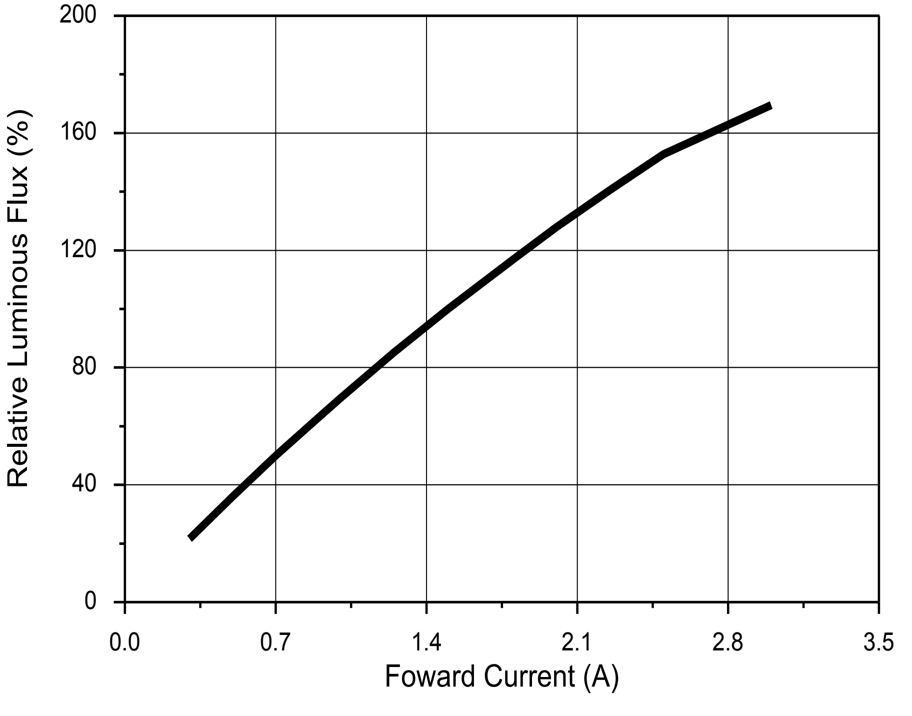


Fig 4. Forward Current vs. Relative Luminous Flux, T_j=25℃



Characteristics Graph

Fig 5. Relative Light Output vs. Junction Temperature, I_F=1.5A

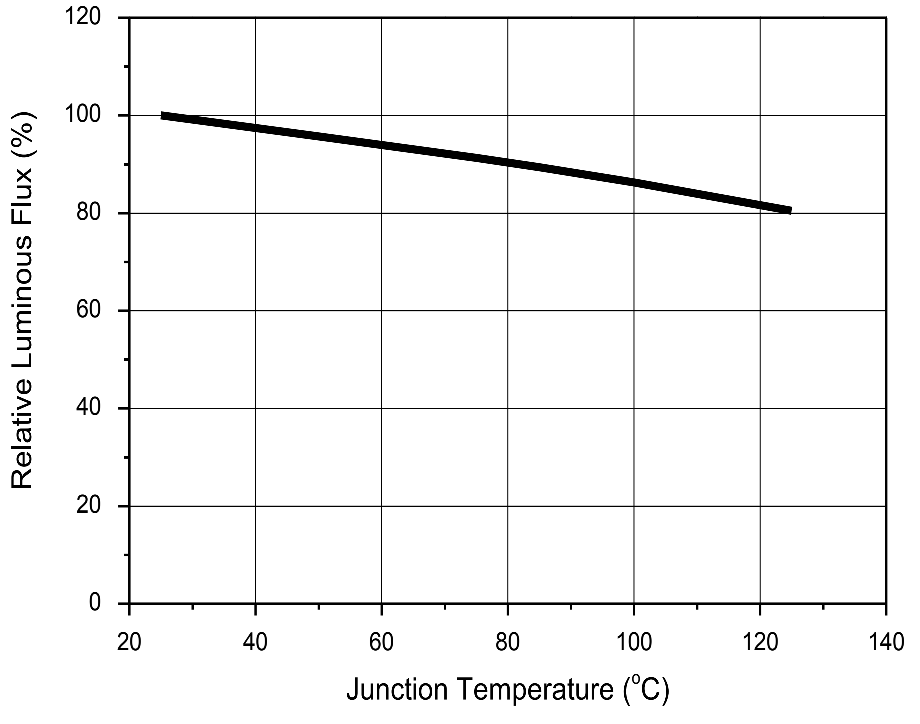
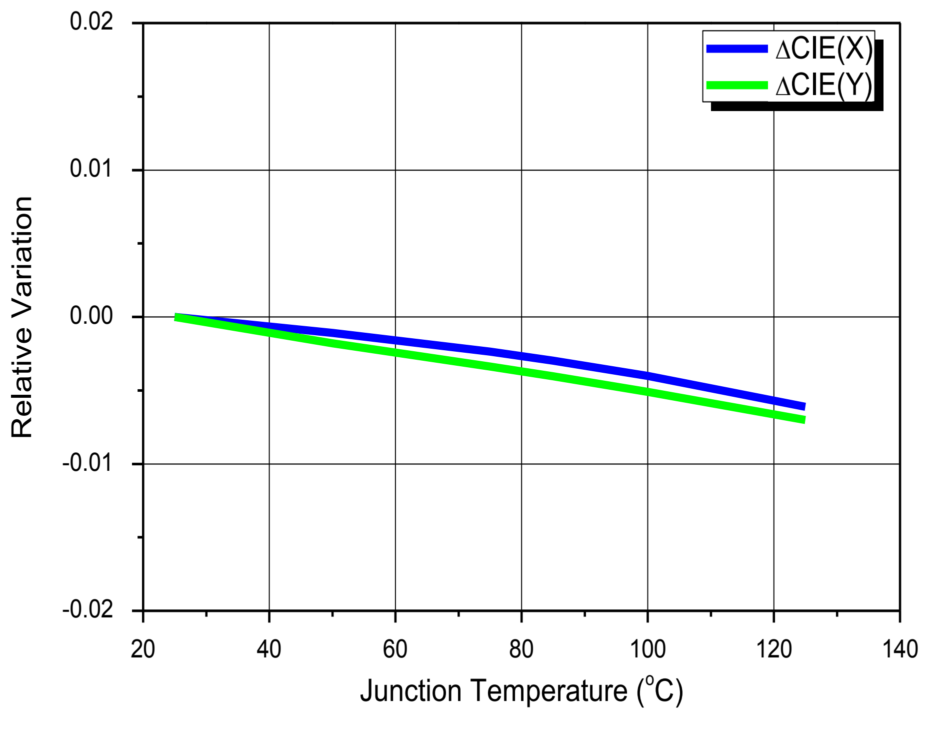
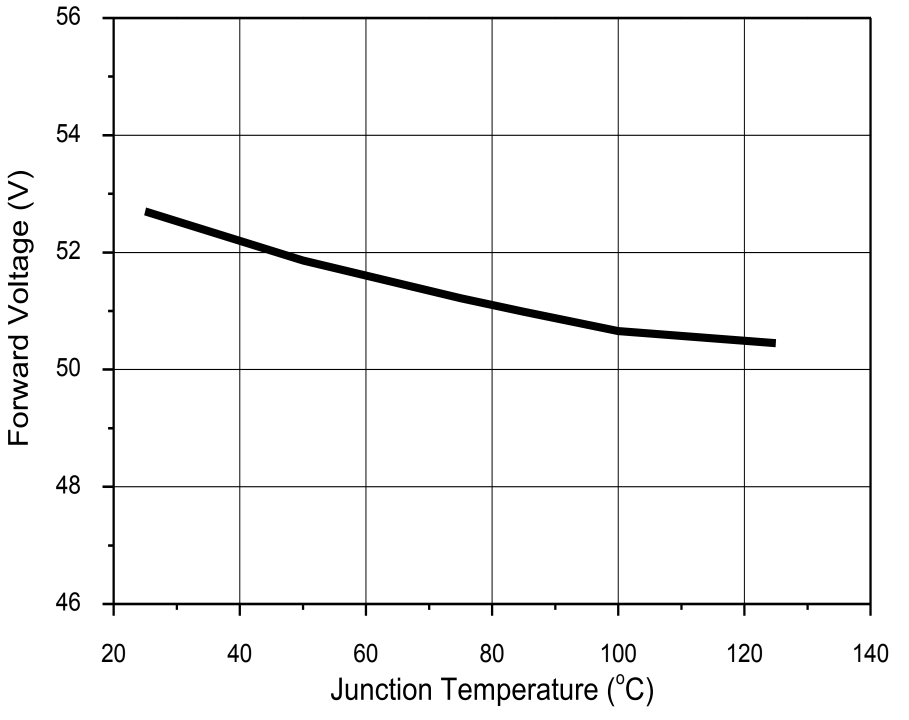


Fig \6. Junction Temperature vs. CIE X, Y Shift, I_F=1.5A (Warm white)



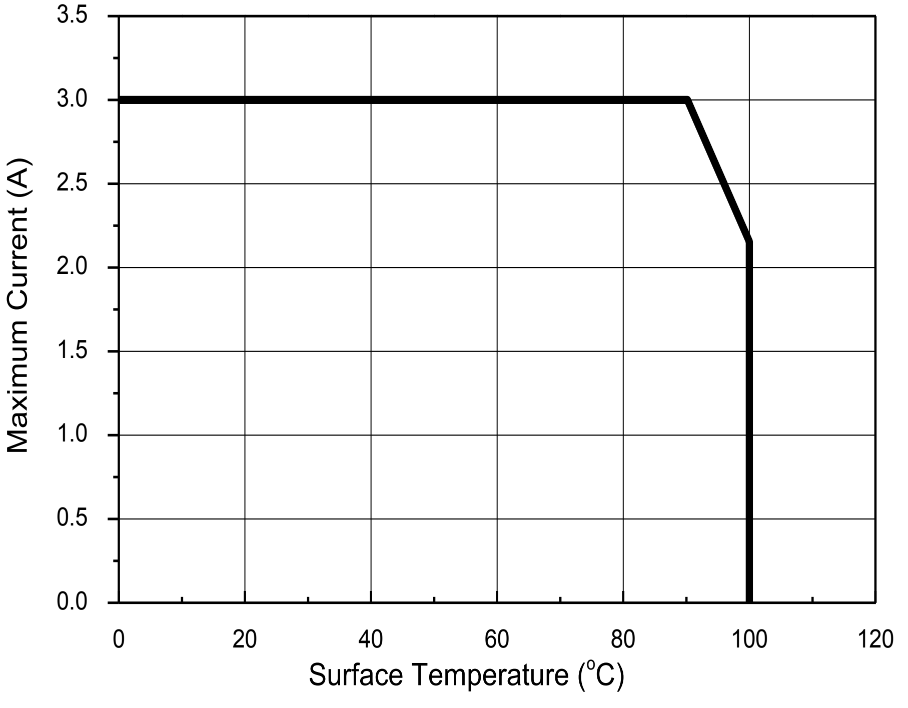
Characteristics Graph

Fig 7. Forward Voltage vs. Junction Temperature, I_F=1.5A



Characteristics Graph

Fig 8. Maximum Forward Current vs. Ambient Temperature, T_j(max.)=125℃, I_F=3A



Color Bin Structure

Table 6. Bin Code description

Part Number	Luminous Flux (lm) @ I_F=1.5A			Color Chromaticity Coordinate @ I_F=1.5A	Typical Forward Voltage (V) @ I_F=1.5A		
	Bin Code	Min.	Max.		Bin Code	Min.	Max.
SDW07F1C	N3	11000	12300	Refer to page. 13 ~ 16	J	51.5	55.5
	O1	12300	13600				
SDW87F1C	N1	8800	9800		K	55.5	59.5
	N2	9800	11000				
	N3	11000	12300				
	O1	12300	13600				

Available ranks

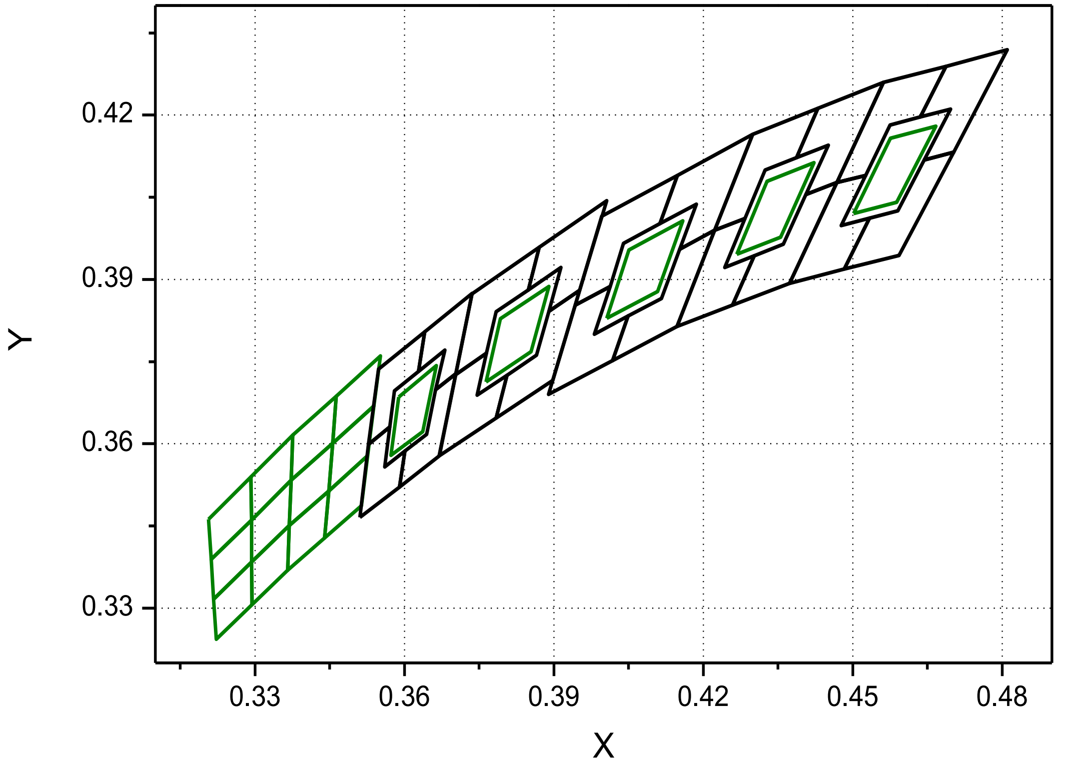
Part Number	CCT	CIE	LF rank				VF rank
SDW07F1C	5300~6000K	B	N1	N2	N3	O1	J
	4700~5300K	C	N1	N2	N3	O1	J
	4200~4700K	D	N1	N2	N3	O1	J
	3700~4200K	E	N1	N2	N3	O1	J
SDW87F1C	5300~6000K	B	N1	N2	N3	O1	J
	4700~5300K	C	N1	N2	N3	O1	J
	4200~4700K	D	N1	N2	N3	O1	J
	3700~4200K	E	N1	N2	N3	O1	J
	3200~3700K	F	N1	N2	N3	O1	J
	2900~3200K	G	N1	N2	N3	O1	J
	2600~2900K	H	N1	N2	N3	O1	J

Notes :

1. Star shape [*] means not available now.

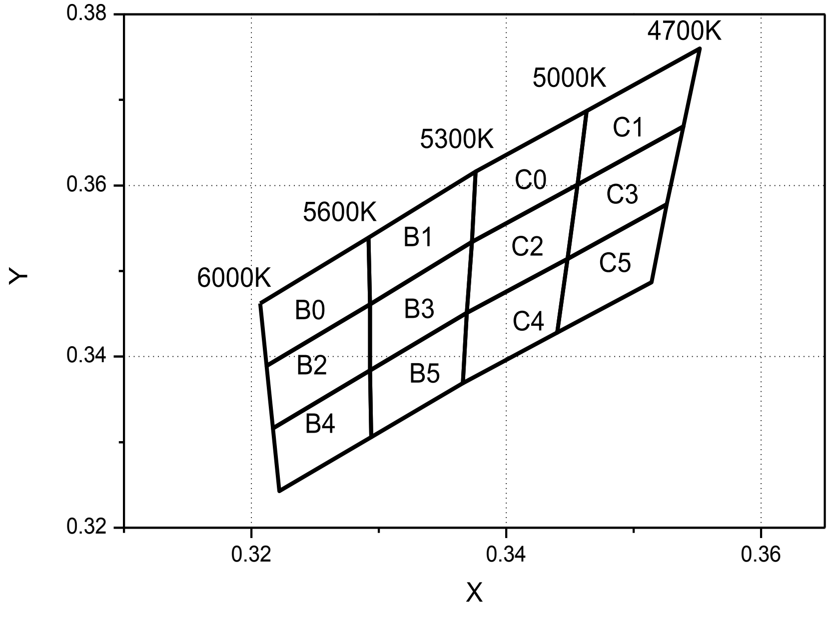
Color Bin Structure

CIE Chromaticity Diagram



Color Bin Structure

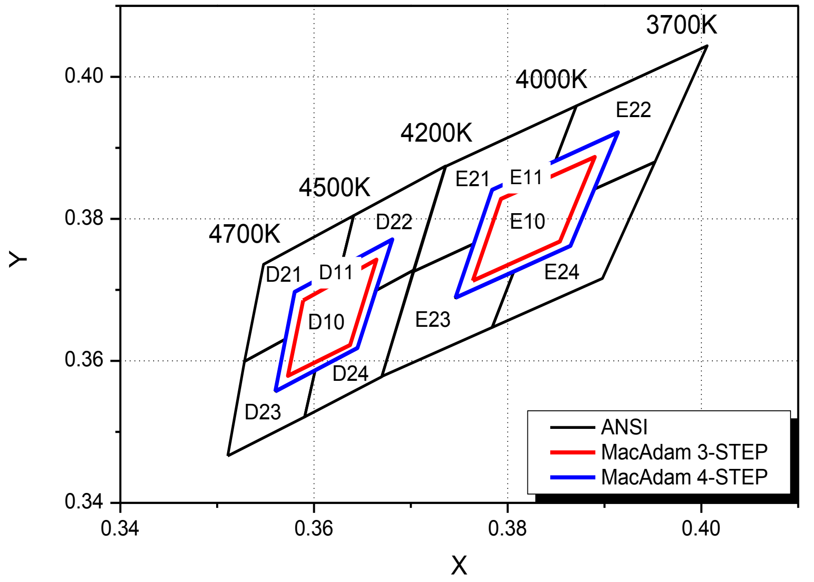
CIE Chromaticity Diagram, T_j=25℃, I_F=1.5A



B0		B1		B2	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3207	0.3462	0.3292	0.3539	0.3212	0.3389
0.3212	0.3389	0.3293	0.3461	0.3217	0.3316
0.3293	0.3461	0.3373	0.3534	0.3293	0.3384
0.3292	0.3539	0.3376	0.3616	0.3293	0.3461
B3		**B4**		**B5**	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3293	0.3461	0.3217	0.3316	0.3293	0.3384
0.3293	0.3384	0.3222	0.3243	0.3294	0.3306
0.3369	0.3451	0.3294	0.3306	0.3366	0.3369
0.3373	0.3534	0.3293	0.3384	0.3369	0.3451
C0		**C1**		**C2**	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3376	0.3616	0.3463	0.3687	0.3373	0.3534
0.3373	0.3534	0.3456	0.3601	0.3369	0.3451
0.3456	0.3601	0.3539	0.3669	0.3448	0.3514
0.3463	0.3687	0.3552	0.3760	0.3456	0.3601
C3		**C4**		**C5**	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3456	0.3601	0.3369	0.3451	0.3448	0.3514
0.3448	0.3514	0.3366	0.3369	0.3440	0.3428
0.3526	0.3578	0.3440	0.3428	0.3514	0.3487
0.3539	0.3669	0.3448	0.3514	0.3526	0.3578

Color Bin Structure

CIE Chromaticity Diagram, T_j=25℃, I_F=1.5A

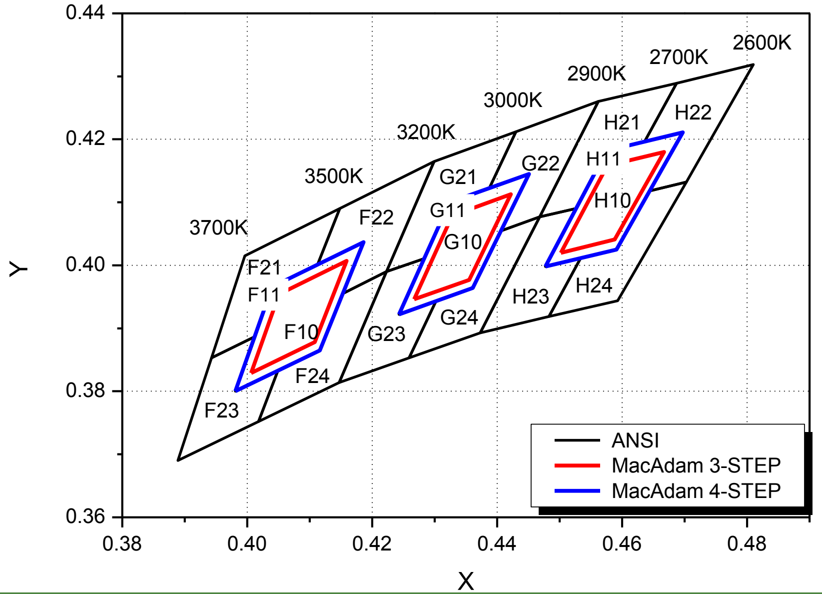


3-STEP				4-STEP			
D10		E10		D11		E11	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3589	0.3685	0.3764	0.3713	0.3560	0.3557	0.3746	0.3689
0.3665	0.3742	0.3793	0.3828	0.3580	0.3697	0.3784	0.3841
0.3637	0.3622	0.3890	0.3887	0.3681	0.3771	0.3914	0.3922
0.3573	0.3579	0.3854	0.3768	0.3645	0.3618	0.3865	0.3762

ANSI							
D21		D22		D23		D24	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3528	0.3599	0.3628	0.3732	0.3601	0.3587	0.3511	0.3466
0.3548	0.3736	0.3641	0.3805	0.3645	0.3618	0.3528	0.3599
0.3641	0.3805	0.3736	0.3874	0.3663	0.3699	0.3570	0.3631
0.3628	0.3732	0.3703	0.3728	0.3703	0.3728	0.3560	0.3558
0.3580	0.3697	0.3663	0.3699	0.3670	0.3578	0.3601	0.3587
0.3570	0.3631	0.3681	0.3771	0.3590	0.3521	0.3590	0.3521
E21		E22		E23		E24	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3703	0.3726	0.3890	0.3842	0.3670	0.3578	0.3784	0.3647
0.3736	0.3874	0.3914	0.3922	0.3703	0.3726	0.3806	0.3725
0.3871	0.3959	0.3849	0.3881	0.3765	0.3765	0.3865	0.3762
0.3849	0.3881	0.3871	0.3959	0.3746	0.3689	0.3890	0.3842
0.3784	0.3841	0.4006	0.4044	0.3806	0.3725	0.3952	0.3880
0.3765	0.3765	0.3952	0.3880	0.3784	0.3647	0.3898	0.3716

Color Bin Structure

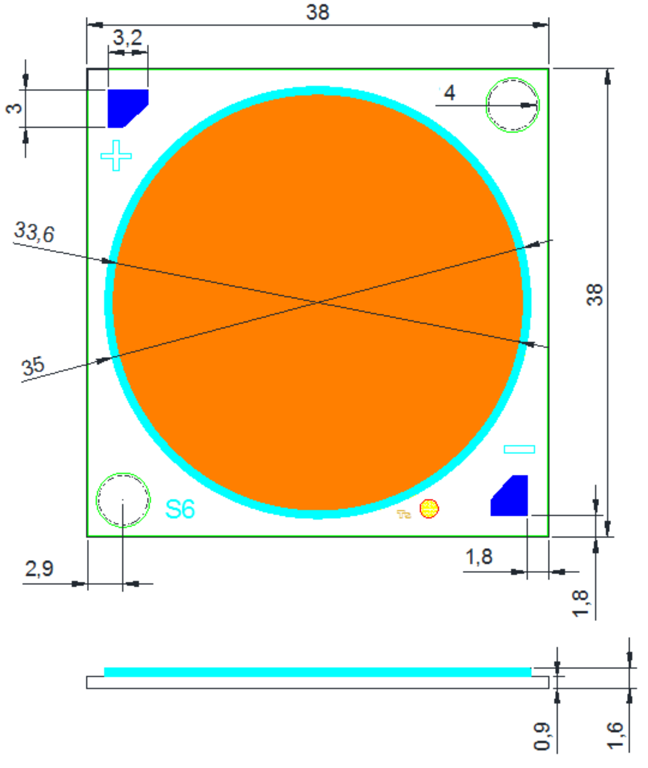
CIE Chromaticity Diagram, T_j=25℃, I_F=1.5A

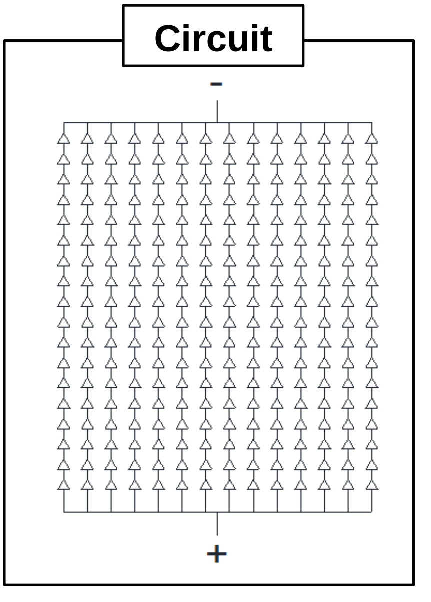


3-STEP						4-STEP					
F10		G10		H10		F11		G11		H11	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.4006	0.3829	0.4267	0.3946	0.4502	0.4020	0.3981	0.3800	0.4243	0.3922	0.4477	0.3998
0.4051	0.3954	0.4328	0.4079	0.4576	0.4158	0.4040	0.3966	0.4324	0.4100	0.4575	0.4182
0.4159	0.4007	0.4422	0.4113	0.4667	0.4180	0.4186	0.4037	0.4451	0.4145	0.4697	0.4211
0.4108	0.3878	0.4355	0.3977	0.4588	0.4041	0.4116	0.3865	0.4361	0.3964	0.4591	0.4025

ANSI							
F21		F22		F23		F24	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.4148	0.4090	0.4013	0.3887	0.4223	0.3990	0.4299	0.4165
0.3996	0.4015	0.3943	0.3853	0.4153	0.3955	0.4148	0.4090
0.3943	0.3853	0.3889	0.3690	0.4116	0.3865	0.4113	0.4002
0.4013	0.3887	0.4018	0.3752	0.4049	0.3833	0.4186	0.4037
0.4040	0.3966	0.4049	0.3833	0.4018	0.3752	0.4153	0.3955
0.4113	0.4002	0.3981	0.3800	0.4147	0.3814	0.4223	0.3990
G21		G22		G23		G24	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.4223	0.3990	0.4406	0.4055	0.4147	0.3814	0.4259	0.3853
0.4299	0.4165	0.4451	0.4145	0.4223	0.3990	0.4302	0.3943
0.4430	0.4212	0.4387	0.4122	0.4284	0.4011	0.4361	0.3964
0.4387	0.4122	0.4430	0.4212	0.4243	0.3922	0.4406	0.4055
0.4324	0.4100	0.4562	0.4260	0.4302	0.3943	0.4468	0.4077
0.4284	0.4011	0.4468	0.4077	0.4259	0.3853	0.4373	0.3893
H21		H22		H23		H24	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.4468	0.4077	0.4644	0.4118	0.4373	0.3893	0.4483	0.3919
0.4562	0.4260	0.4697	0.4211	0.4468	0.4077	0.4534	0.4012
0.4687	0.4289	0.4636	0.4197	0.4526	0.4090	0.4591	0.4025
0.4636	0.4197	0.4687	0.4289	0.4477	0.3998	0.4644	0.4118
0.4575	0.4182	0.4810	0.4319	0.4534	0.4012	0.4703	0.4132
0.4526	0.4090	0.4703	0.4132	0.4483	0.3919	0.4593	0.3944

Mechanical Dimensions

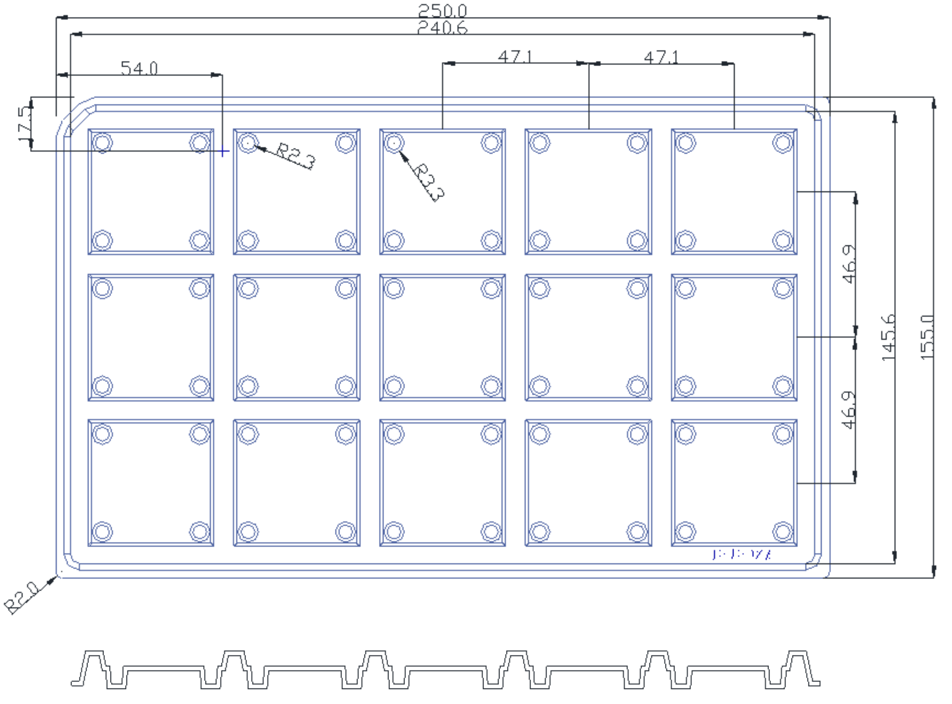




Notes :

1. All dimensions are in millimeters.
2. Scale : none
3. Undefined tolerance is ±0.3mm

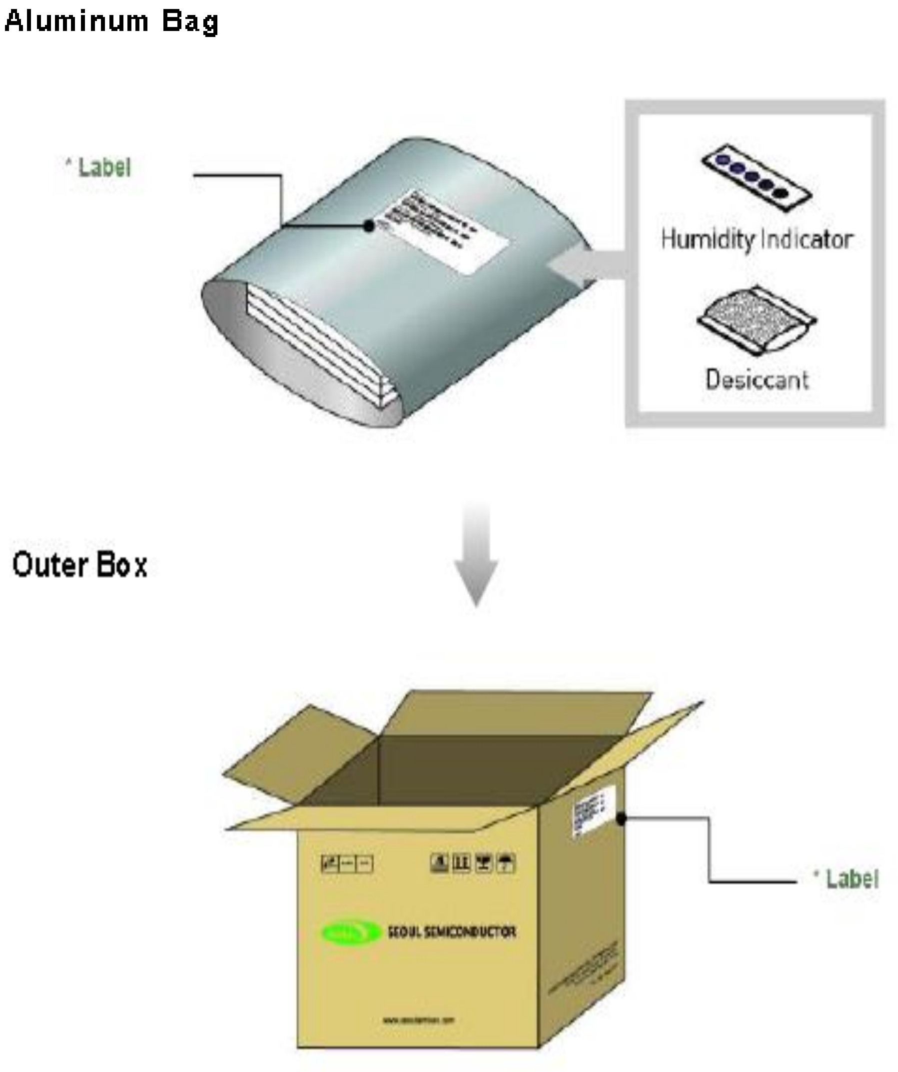
Packaging Specification



Notes :

1. Quantity : 15pcs/Tray
2. All dimensions are in millimeters (tolerance : ±0.3)
3. Scale none

Packaging Specification



Notes :

(1) Heat Sealed after packing (Use Zipper Bag)

(2) Quantity : min 8Tray(120pcs) ~ max 20Tray(300pcs) /Bag

Product Nomenclature

Table 4. Part Numbering System : $X_1X_2X_3\ X_4X_5\ X_6X_7\ X_8$

Part Number Code	Description	Part Number	Value
X_1	Company	S	
X_2	Package series	D	
X_3X_4	Color Specification	W0	CRI 70
		W8	CRI 80
X_5	Series number	**7**	
X_6	Lens type	F	Flat
X_7	PCB type	1	PCB
X_8	Revision number	C	New COB type

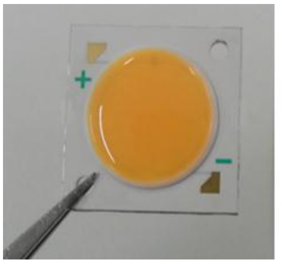
Table 5. Lot Numbering System : $Y_1Y_2Y_3Y_4Y_5Y_6\ Y_7Y_8Y_9Y_{10} – Y_{11}Y_{12}Y_{13}Y_{14}Y_{15}Y_{16}Y_{17}$

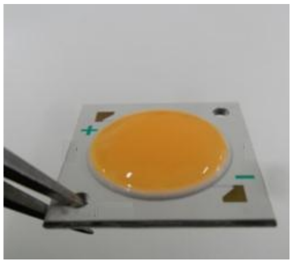
Lot Number Code	Description
$Y_1Y_2Y_3Y_4Y_5$	Date of box packing
$Y_6Y_7Y_8Y_9Y_{10}$	Date of label order
$Y_{11}Y_{12}Y_{13}Y_{14}Y_{15}Y_{16}Y_{17}$	Item code

Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.

(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.





(3) Silicone differs from materials conventionally used for the manufacturing of LEDs.

These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust. As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of wire.

(4) Seoul Semiconductor suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.

(5) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this product with acid or sulfur material in sealed space.

(6) Avoid leaving fingerprints on silicone resin parts.

Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend storing Power LEDs in a dry box with a desiccant.

(2) For manual soldering

Seoul Semiconductor recommends the soldering condition

(ZC series product is not adaptable to reflow process)

a. Use lead-free soldering

b. Soldering should be implemented using a soldering equipment at temperature lower than 350°C.

c. Before proceeding the next step, product temperature must be stabilized at room temperature.

(3) Components should not be mounted on warped (non coplanar) portion of PCB.

(4) Radioactive exposure is not considered for the products listed here in.

(5) It is dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.

(6) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.

(7) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

(8) The appearance and specifications of the product may be modified for improvement without notice.

(9) Long time exposure of sun light or occasional UV exposure will cause silicone discoloration.

(10) Attaching LEDs, do not use adhesive that outgas organic vapor.

(11) The driving circuit must be designed to allow forward voltage only when it is ON or OFF. If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.

(12) Please do not touch any of the circuit board, components or terminals with bare hands or metal while circuit is electrically active.

Precaution for Use

(13) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.

(14) LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS). Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.

Ⅰ. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event.
One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:
- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:
- Humidity control (ESD gets worse in a dry environment)

Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
  (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package
  (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.

c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:

- A surge protection circuit
- An appropriately rated over voltage protection device
- A current limiting device

Company Information

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Seoul Semiconductor (SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", deep UV LEDs, "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs. The company's broad product portfolio includes a wide array of package and device choices such as Acrich, high-brightness LEDs, mid-power LEDs, side-view LEDs, through-hole type LED lamps, custom displays, and sensors. The company is vertically integrated from epitaxial growth and chip manufacture in it's fully owned subsidiary, Seoul Viosys, through packaged LEDs and LED modules in three Seoul Semiconductor manufacturing facilities. Seoul Viosys also manufactures a wide range of unique deep-UV wavelength devices.

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